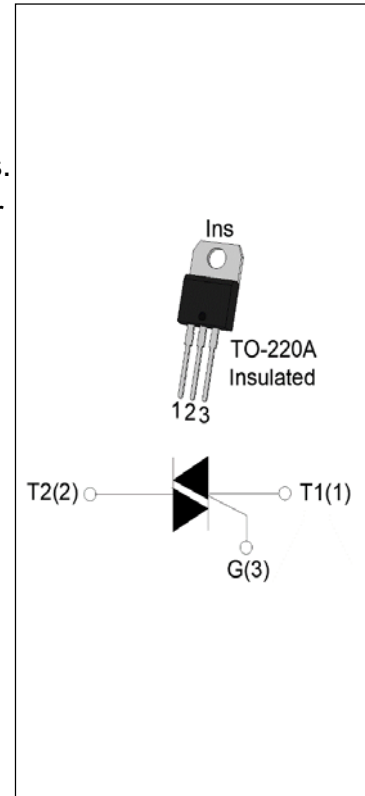


**JST16A-800BW 16A TRIAC**

Rev.A.1.2

**DESCRIPTION:**

The JST16A-800BW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST16A-800BW snubberless triac is especially recommended for use on inductive loads. By using an internal ceramic pad, JST16A-800BW provides a rated insulation voltage of 2500 VRMS, complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.


**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
$V_{DRM}/V_{RRM}$	800	V
$I_{GT\ I/II/III}$	50/50/50	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	°C
Operating junction temperature range	$T_j$	-40-125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{DRM}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{RRM}$	800	V
RMS on-state current ( $T_c \leq 102^\circ\text{C}$ )	$I_{T(RMS)}$	16	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{TSM}$	160	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )		176	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	128	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ )	$di/dt$	100	$\text{A}/\mu\text{s}$
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )	$I_{GM}$	4	A
Average gate power dissipation ( $T_j=125^\circ\text{C}$ )	$P_{G(AV)}$	0.5	W

Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25^{\circ}C$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	4	kV

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^{\circ}C$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12V R_L=33\Omega$	I - II -III	MAX.	50	mA
$V_{GT}$		I - II -III	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM} T_j=125^{\circ}C$ $R_L=3.3k\Omega$	I - II -III	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	I -III	MAX.	70	mA
		II		80	
$I_H$	$I_T=500mA$		MAX.	50	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125^{\circ}C$		MIN.	1500	V/ $\mu s$
(dI/dt) <sub>c</sub>	(dV/dt) <sub>c</sub> =20V/ $\mu s$ $T_j=125^{\circ}C$		MIN.	18	A/ms
$t_{on}$	$I_G=80mA I_A=400mA I_R=40mA$ $T_j=25^{\circ}C$		TYP.	10	$\mu s$
$t_{off}$				70	

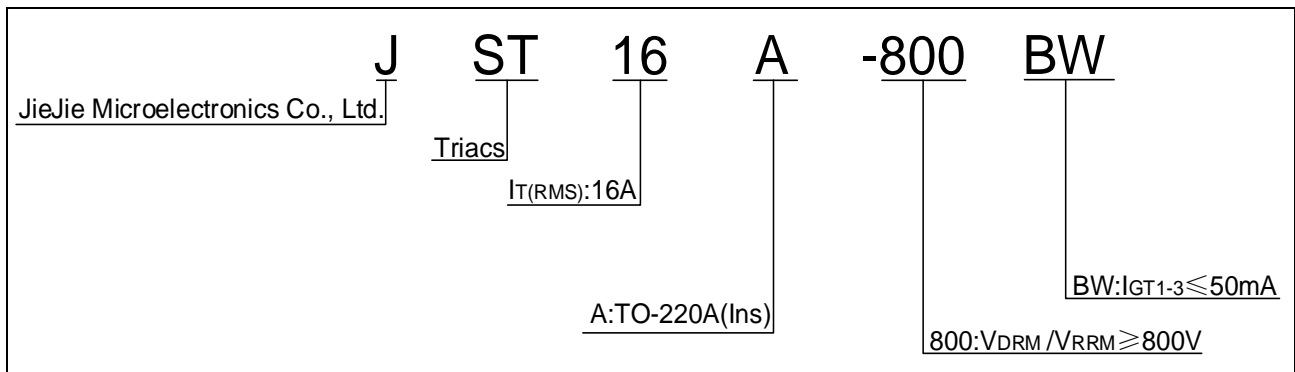
**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=22.5A t_p=380\mu s$	$T_j=25^{\circ}C$	1.5	V
$V_{TO}$	Threshold voltage	$T_j=125^{\circ}C$	0.77	V
$R_D$	Dynamic resistance	$T_j=125^{\circ}C$	30	m $\Omega$
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}C$	5	$\mu A$
$I_{RRM}$		$T_j=125^{\circ}C$	0.5	mA

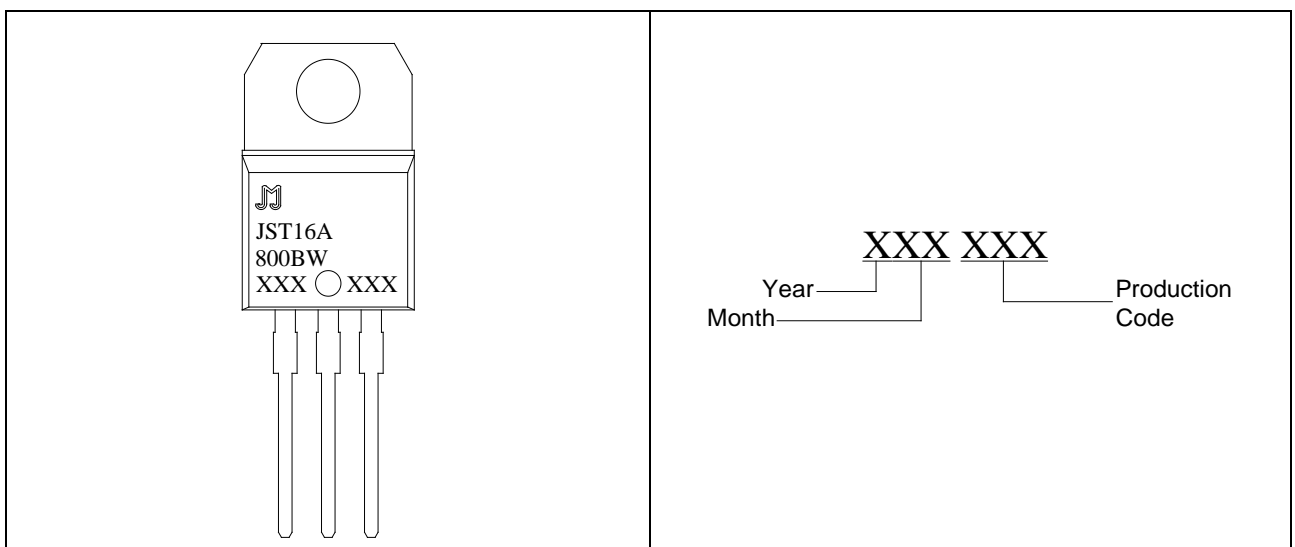
**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1	$^{\circ}C/W$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^{\circ}C/W$

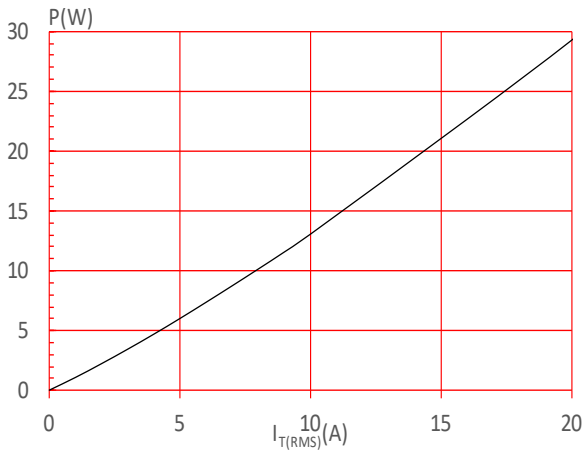
**ORDERING INFORMATION**



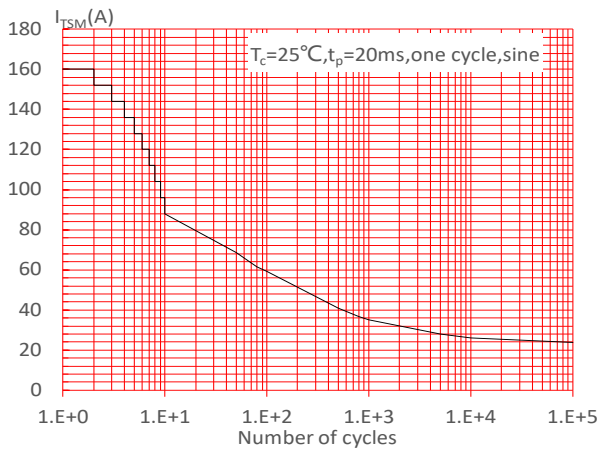
**MARKING**



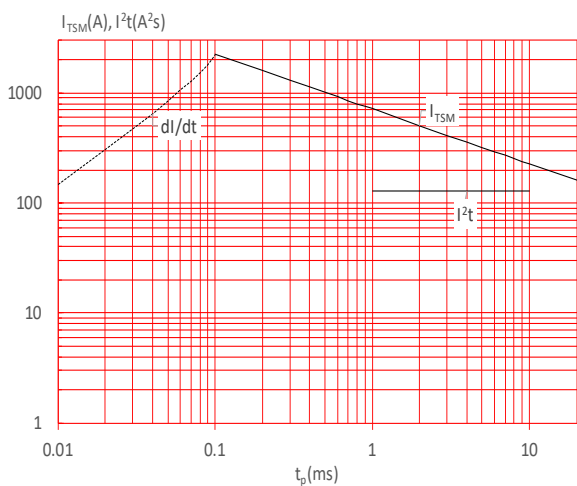
**FIG.1:** Maximum power dissipation versus RMS on-state current



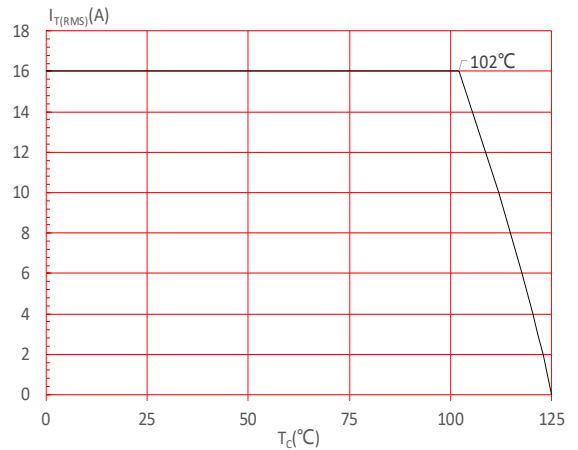
**FIG.3:** Surge peak on-state current versus number of cycles



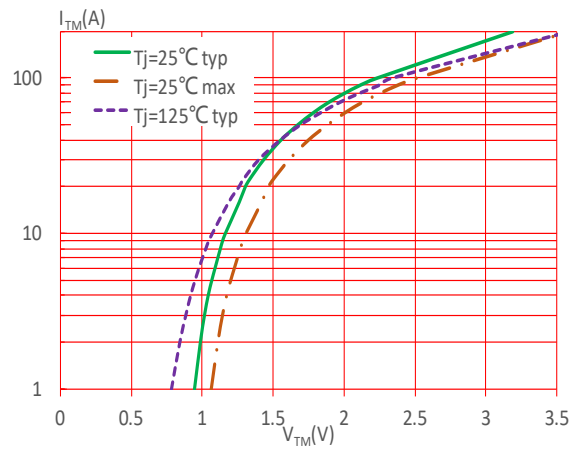
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $di/dt < 100\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

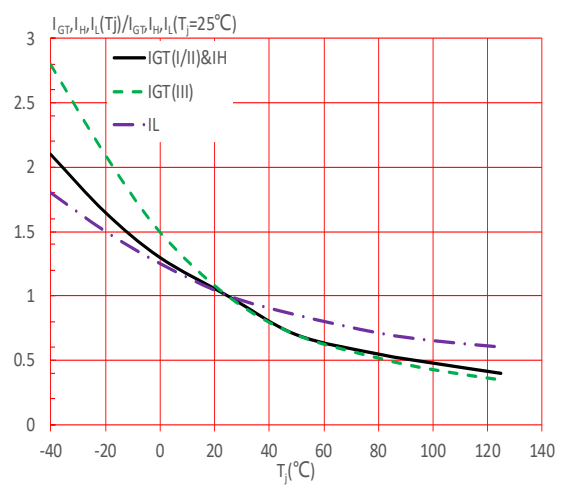
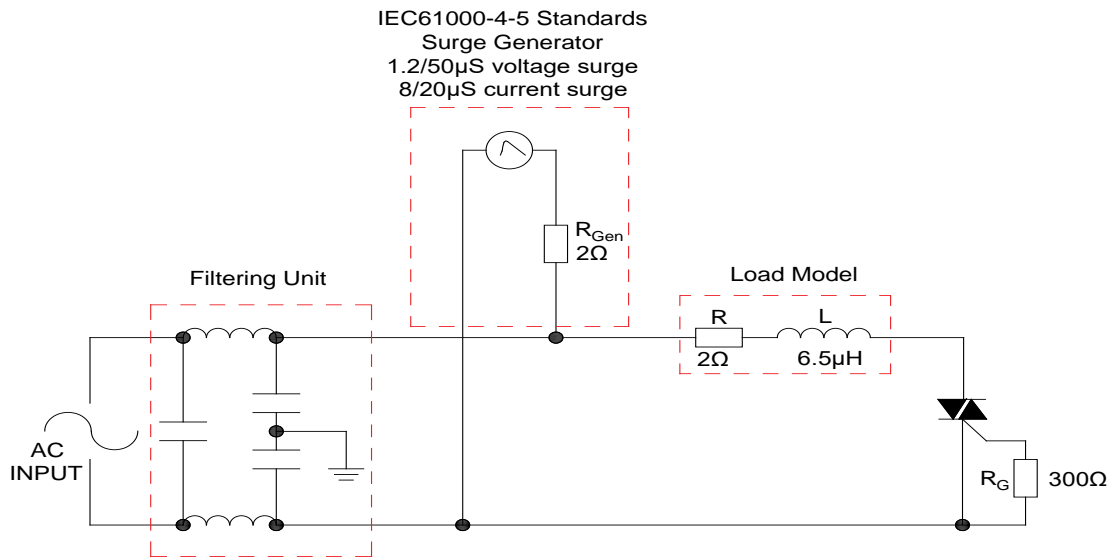


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



### LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics

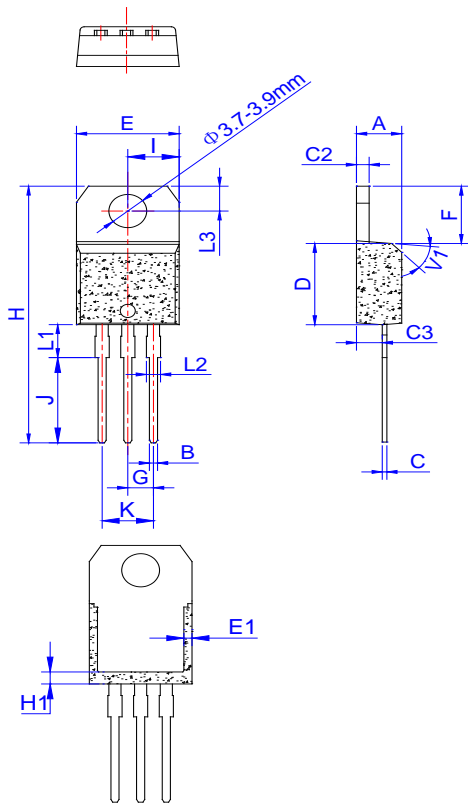
## ORDERING INFORMATION

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I - II - III			
JST16A-800BW	800	50	TO-220A(Ins)	50	Tube

## Document Revision History

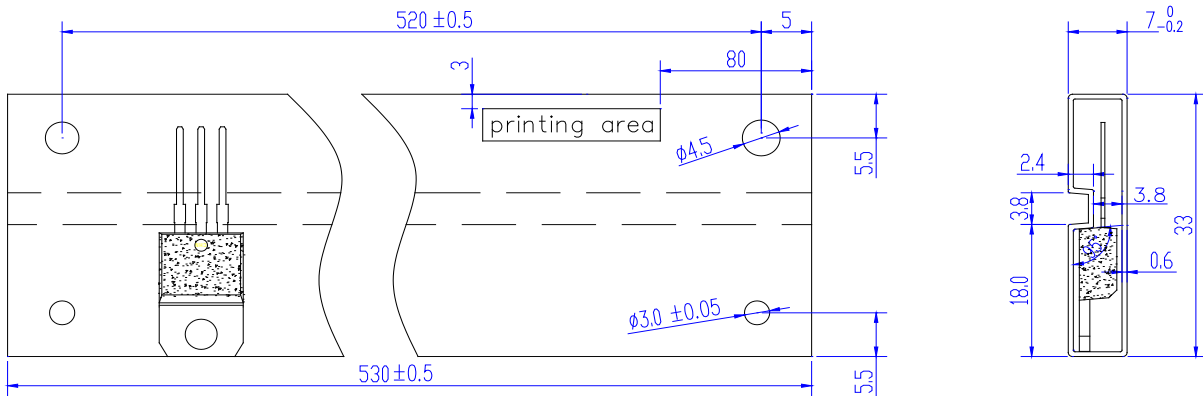
Date	Revision	Changes
Apr.12, 2023	A.1.0	Last updated
Oct.13, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA
Jan.23, 2026	A.1.2	Revise $R_{th(j-c)}$

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.40	0.386		0.409
E1	1.00		1.40	0.039		0.055
F	6.25		6.85	0.246		0.270
G	2.40		2.70	0.094		0.106
H	28.00		29.80	1.102		1.173
H1	1.80		2.20	0.071		0.087
I	4.80		5.20	0.189		0.205
J	9.55		9.95	0.376		0.392
K	4.80		5.20	0.189		0.205
L1	3.45		4.05	0.136		0.159
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220A	TUBE	50	1,000	5,000

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